

MJE200 NPN
MJE210 PNP

**COMPLEMENTARY SILICON
POWER TRANSISTORS**



TO-18 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR MJE200, MJE210 types are complementary silicon transistors designed for high gain amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Peak Collector Current
Continuous Base Current
Power Dissipation
Power Dissipation ($T_C=25^\circ\text{C}$)
Operating and Storage Junction Temperature
Thermal Resistance
Thermal Resistance

SYMBOL		UNITS
V_{CBO}	40	V
V_{CEO}	25	V
V_{EBO}	8.0	V
I_C	5.0	A
I_{CM}	10	A
I_B	1.0	A
P_D	1.5	W
P_D	15	W
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	83.4	$^\circ\text{C/W}$
θ_{JC}	8.34	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=40\text{V}$		100	nA
I_{CBO}	$V_{CB}=40\text{V}, T_J=125^\circ\text{C}$		100	μA
I_{EBO}	$V_{EB}=8.0\text{V}$		100	nA
BV_{CEO}	$I_C=10\text{mA}$	25		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		0.75	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		1.8	V
$V_{BE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		2.5	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=2.0\text{A}$		1.6	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	70		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=2.0\text{A}$	45	180	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$	10		
f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=10\text{MHz}$	65		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (MJE200)		80	pF
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (MJE210)		120	pF

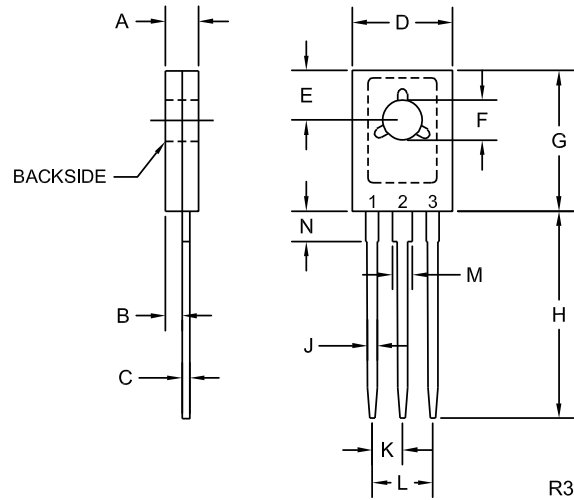
R1 (2-May 2012)

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TO-126 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base

MARKING:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.094	0.110	2.40	2.80
B	0.050		1.27	
C	0.015	0.030	0.38	0.75
D	0.291	0.335	7.40	8.50
E	0.148		3.75	
F	0.118	0.134	3.00	3.40
G	0.413	0.472	10.50	12.00
H	0.618		15.70	
J	0.024	0.035	0.62	0.90
K	0.089		2.25	
L	0.177		4.50	
M	0.045	0.055	1.14	1.40
N	0.083		2.10	

TO-126 (REV:R3)

R1 (2-May 2012)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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